

# NSS12600CF8T1G

## 12 V, 6.0 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e<sup>2</sup>PowerEdge family of low  $V_{CE(sat)}$  transistors are miniature surface mount devices featuring ultra low saturation voltage ( $V_{CE(sat)}$ ) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e<sup>2</sup>PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

- This is a Pb-Free Device

### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

| Rating                         | Symbol    | Max                        | Unit |
|--------------------------------|-----------|----------------------------|------|
| Collector-Emitter Voltage      | $V_{CEO}$ | -12                        | Vdc  |
| Collector-Base Voltage         | $V_{CBO}$ | -12                        | Vdc  |
| Emitter-Base Voltage           | $V_{EBO}$ | -7.0                       | Vdc  |
| Collector Current - Continuous | $I_C$     | -5.0                       | Adc  |
| Collector Current - Peak       | $I_{CM}$  | -6.0                       | A    |
| Electrostatic Discharge        | ESD       | HBM Class 3B<br>MM Class C |      |

### THERMAL CHARACTERISTICS

| Characteristic                                                                        | Symbol                                | Max            | Unit                       |
|---------------------------------------------------------------------------------------|---------------------------------------|----------------|----------------------------|
| Total Device Dissipation, $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$ (Note 1)                        | 830<br>6.7     | mW<br>mW/ $^\circ\text{C}$ |
| Thermal Resistance,<br>Junction-to-Ambient                                            | $R_{\theta JA}$ (Note 1)              | 150            | $^\circ\text{C}/\text{W}$  |
| Total Device Dissipation, $T_A = 25^\circ\text{C}$<br>Derate above $25^\circ\text{C}$ | $P_D$ (Note 2)                        | 1.4<br>11.1    | W<br>mW/ $^\circ\text{C}$  |
| Thermal Resistance,<br>Junction-to-Ambient                                            | $R_{\theta JA}$ (Note 2)              | 90             | $^\circ\text{C}/\text{W}$  |
| Thermal Resistance,<br>Junction-to-Lead #1                                            | $R_{\theta JL}$ (Note 2)              | 15             | $^\circ\text{C}/\text{W}$  |
| Total Device Dissipation<br>(Single Pulse < 10 sec)                                   | $P_{D\text{single}}$<br>(Notes 2 & 3) | 2.75           | W                          |
| Junction and Storage<br>Temperature Range                                             | $T_J, T_{stg}$                        | -55 to<br>+150 | $^\circ\text{C}$           |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

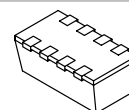
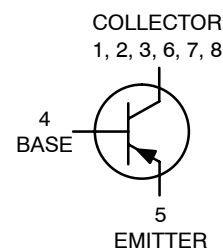
1. FR-4 @ 100 mm<sup>2</sup>, 1 oz copper traces.
2. FR-4 @ 500 mm<sup>2</sup>, 1 oz copper traces.
3. Thermal response.



ON Semiconductor®

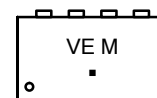
<http://onsemi.com>

### -12 VOLTS, 6.0 AMPS PNP LOW $V_{CE(sat)}$ TRANSISTOR EQUIVALENT $R_{DS(on)}$ 45 m $\Omega$



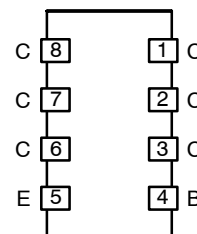
ChipFET™  
CASE 1206A  
STYLE 4

### MARKING DIAGRAM



VE = Specific Device Code  
M = Date Code  
■ = Pb-Free Package

### PIN CONNECTIONS



### ORDERING INFORMATION

| Device         | Package              | Shipping†            |
|----------------|----------------------|----------------------|
| NSS12600CF8T1G | ChipFET<br>(Pb-Free) | 3000/<br>Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NSS12600CF8T1G

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

| Characteristic                                                                         | Symbol               | Min  | Typical | Max  | Unit |
|----------------------------------------------------------------------------------------|----------------------|------|---------|------|------|
| <b>OFF CHARACTERISTICS</b>                                                             |                      |      |         |      |      |
| Collector – Emitter Breakdown Voltage<br>(I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0) | V <sub>(BR)CEO</sub> | -12  | –       | –    | Vdc  |
| Collector – Base Breakdown Voltage<br>(I <sub>C</sub> = -0.1 mA, I <sub>E</sub> = 0)   | V <sub>(BR)CBO</sub> | -12  | –       | –    | Vdc  |
| Emitter – Base Breakdown Voltage<br>(I <sub>E</sub> = -0.1 mA, I <sub>C</sub> = 0)     | V <sub>(BR)EBO</sub> | -7.0 | –       | –    | Vdc  |
| Collector Cutoff Current<br>(V <sub>CE</sub> = -12 V, I <sub>E</sub> = 0)              | I <sub>CBO</sub>     | –    | –       | -0.1 | μA   |
| Emitter Cutoff Current<br>(V <sub>EB</sub> = -7.0 V)                                   | I <sub>EBO</sub>     | –    | –       | -0.1 | μA   |

## ON CHARACTERISTICS

|                                                                                                                                                                                                                                                                                                                                                                                                          |                      |                                 |                                                          |                                                          |     |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------|---------------------------------|----------------------------------------------------------|----------------------------------------------------------|-----|
| DC Current Gain (Note 4)<br>(I <sub>C</sub> = -10 mA, V <sub>CE</sub> = -2.0 V)<br>(I <sub>C</sub> = -500 mA, V <sub>CE</sub> = -2.0 V)<br>(I <sub>C</sub> = -1.0 A, V <sub>CE</sub> = -2.0 V)<br>(I <sub>C</sub> = -2.0 A, V <sub>CE</sub> = -2.0 V)<br>(I <sub>C</sub> = -3.0 A, V <sub>CE</sub> = -2.0 V)                                                                                             | h <sub>FE</sub>      | 250<br>250<br>250<br>200<br>180 | –<br>–<br>300<br>–<br>–                                  | –<br>–<br>–<br>–<br>–                                    |     |
| Collector – Emitter Saturation Voltage (Note 4)<br>(I <sub>C</sub> = -0.1 A, I <sub>B</sub> = -0.010 A) (Note 5)<br>(I <sub>C</sub> = -1.0 A, I <sub>B</sub> = -0.100 A)<br>(I <sub>C</sub> = -1.0 A, I <sub>B</sub> = -0.010 A)<br>(I <sub>C</sub> = -2.0 A, I <sub>B</sub> = -0.020 A)<br>(I <sub>C</sub> = -3.0 A, I <sub>B</sub> = -0.030 A)<br>(I <sub>C</sub> = -4.0 A, I <sub>B</sub> = -0.400 A) | V <sub>CE(sat)</sub> | –<br>–<br>–<br>–<br>–<br>–      | -0.005<br>-0.045<br>-0.070<br>-0.095<br>-0.120<br>-0.140 | -0.010<br>-0.060<br>-0.080<br>-0.120<br>-0.160<br>-0.170 | V   |
| Base – Emitter Saturation Voltage (Note 4)<br>(I <sub>C</sub> = -1.0 A, I <sub>B</sub> = -0.01 A)                                                                                                                                                                                                                                                                                                        | V <sub>BE(sat)</sub> | –                               | –                                                        | -0.90                                                    | V   |
| Base – Emitter Turn-on Voltage (Note 4)<br>(I <sub>C</sub> = -2.0 A, V <sub>CE</sub> = -3.0 V)                                                                                                                                                                                                                                                                                                           | V <sub>BE(on)</sub>  | –                               | –                                                        | -0.90                                                    | V   |
| Cutoff Frequency<br>(I <sub>C</sub> = -100 mA, V <sub>CE</sub> = -5.0 V, f = 100 MHz)                                                                                                                                                                                                                                                                                                                    | f <sub>T</sub>       | 100                             | –                                                        | –                                                        | MHz |
| Input Capacitance (V <sub>EB</sub> = -0.5 V, f = 1.0 MHz)                                                                                                                                                                                                                                                                                                                                                | C <sub>ibo</sub>     | –                               | –                                                        | 800                                                      | pF  |
| Output Capacitance (V <sub>CB</sub> = -3.0 V, f = 1.0 MHz)                                                                                                                                                                                                                                                                                                                                               | C <sub>obo</sub>     | –                               | –                                                        | 300                                                      | pF  |

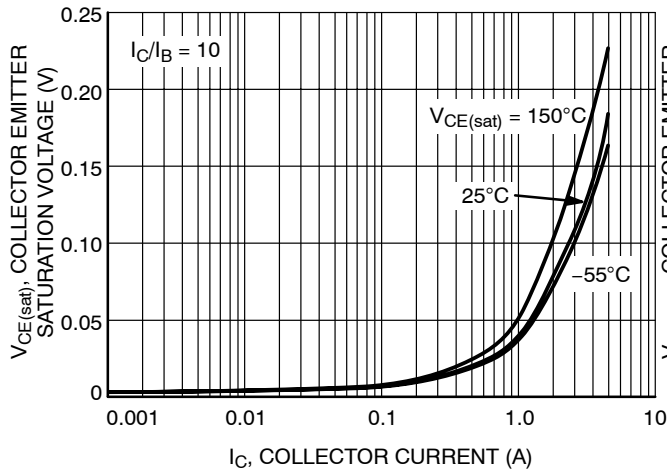
## SWITCHING CHARACTERISTICS

|                                                                                     |                |   |   |     |    |
|-------------------------------------------------------------------------------------|----------------|---|---|-----|----|
| Delay (V <sub>CC</sub> = -10 V, I <sub>C</sub> = 750 mA, I <sub>B1</sub> = 15 mA)   | t <sub>d</sub> | – | – | 130 | ns |
| Rise (V <sub>CC</sub> = -10 V, I <sub>C</sub> = 750 mA, I <sub>B1</sub> = 15 mA)    | t <sub>r</sub> | – | – | 220 | ns |
| Storage (V <sub>CC</sub> = -10 V, I <sub>C</sub> = 750 mA, I <sub>B1</sub> = 15 mA) | t <sub>s</sub> | – | – | 350 | ns |
| Fall (V <sub>CC</sub> = -10 V, I <sub>C</sub> = 750 mA, I <sub>B1</sub> = 15 mA)    | t <sub>f</sub> | – | – | 240 | ns |

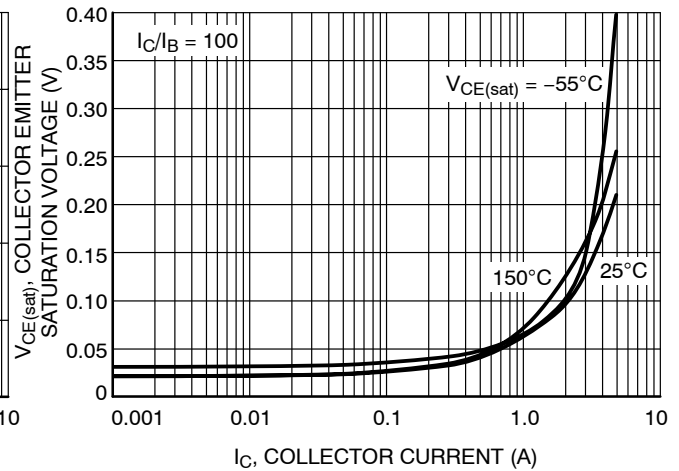
4. Pulsed Condition: Pulse Width = 300 μsec, Duty Cycle ≤ 2%.

5. Guaranteed by design but not tested.

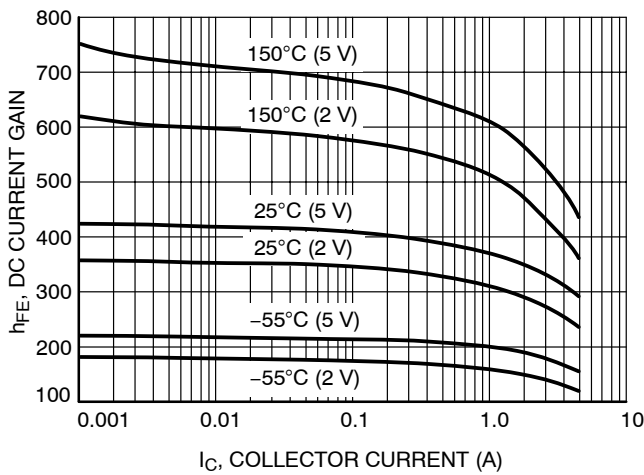
# NSS12600CF8T1G



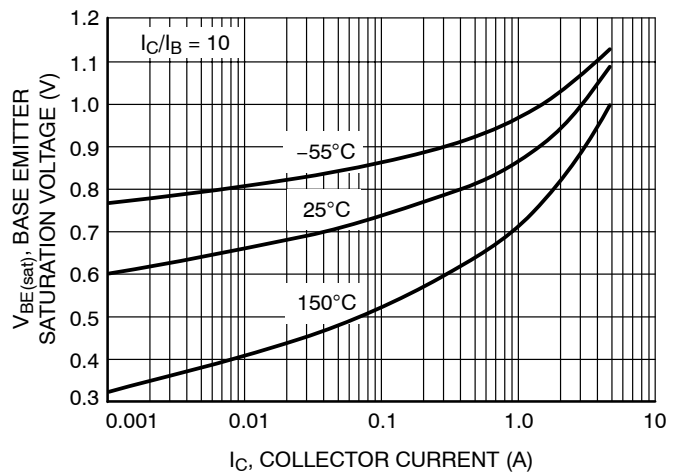
**Figure 1. Collector Emitter Saturation Voltage vs. Collector Current**



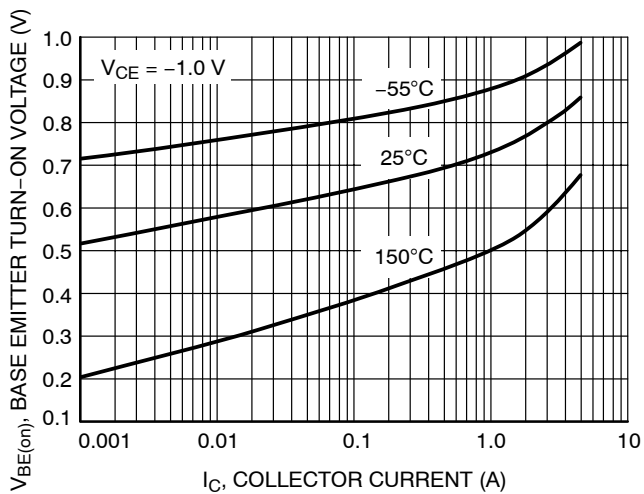
**Figure 2. Collector Emitter Saturation Voltage vs. Collector Current**



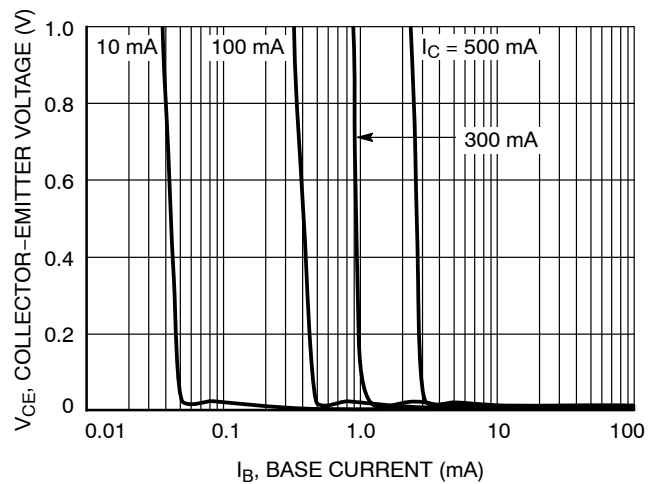
**Figure 3. DC Current Gain vs. Collector Current**



**Figure 4. Base Emitter Saturation Voltage vs. Collector Current**

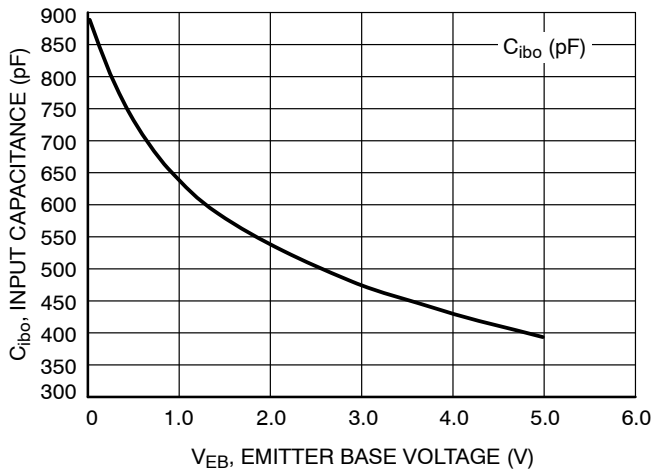


**Figure 5. Base Emitter Turn-On Voltage vs. Collector Current**

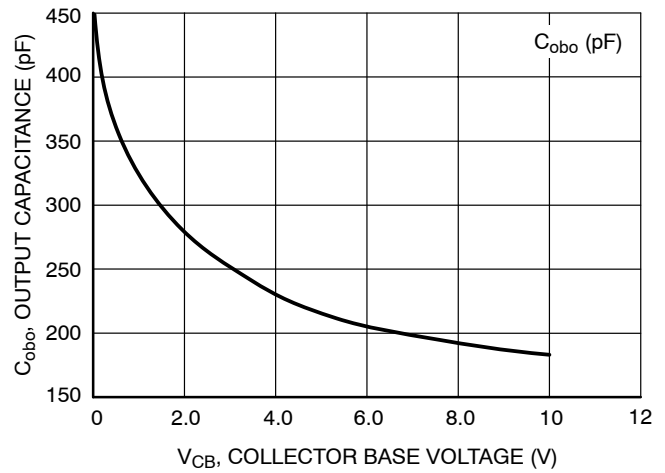


**Figure 6. Saturation Region**

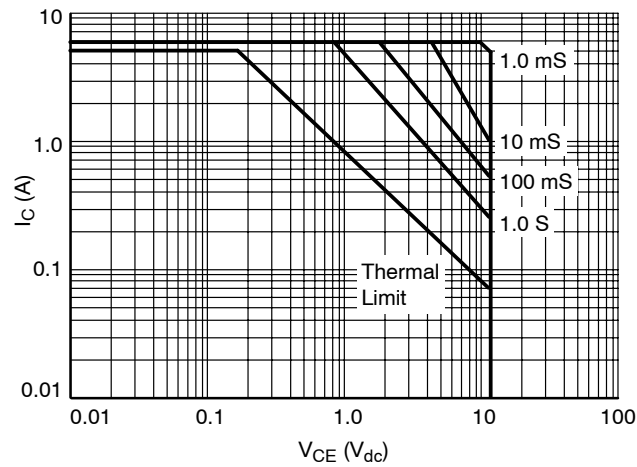
# NSS12600CF8T1G



**Figure 7. Input Capacitance**



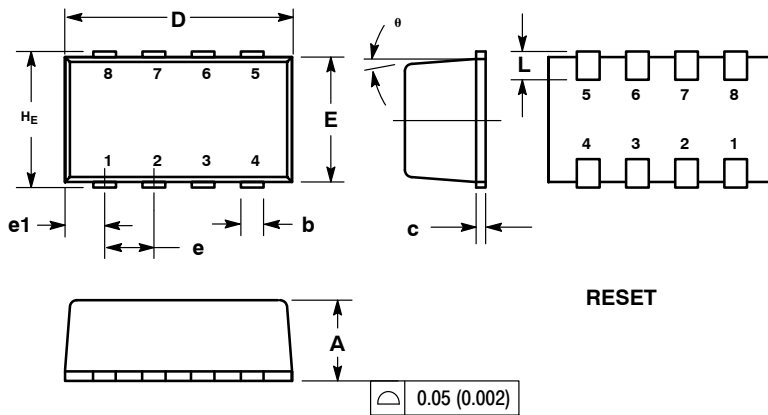
**Figure 8. Output Capacitance**



**Figure 9. Safe Operating Area**



SCALE 1:1



ChipFET™  
CASE1206A-03  
ISSUE K

DATE 19 MAY 2009

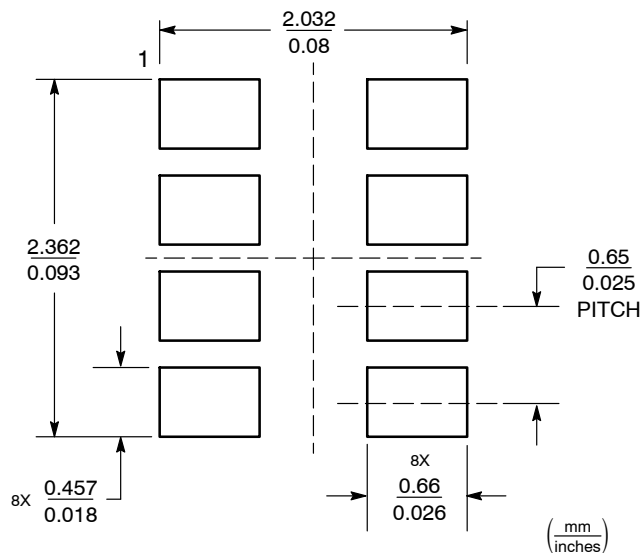
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

| DIM | MILLIMETERS |      |      | INCHES    |       |       |
|-----|-------------|------|------|-----------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN       | NOM   | MAX   |
| A   | 1.00        | 1.05 | 1.10 | 0.039     | 0.041 | 0.043 |
| b   | 0.25        | 0.30 | 0.35 | 0.010     | 0.012 | 0.014 |
| c   | 0.10        | 0.15 | 0.20 | 0.004     | 0.006 | 0.008 |
| D   | 2.95        | 3.05 | 3.10 | 0.116     | 0.120 | 0.122 |
| E   | 1.55        | 1.65 | 1.70 | 0.061     | 0.065 | 0.067 |
| e   | 0.65 BSC    |      |      | 0.025 BSC |       |       |
| e1  | 0.55 BSC    |      |      | 0.022 BSC |       |       |
| L   | 0.28        | 0.35 | 0.42 | 0.011     | 0.014 | 0.017 |
| H_E | 1.80        | 1.90 | 2.00 | 0.071     | 0.075 | 0.079 |
| θ   | 5° NOM      |      |      | 5° NOM    |       |       |

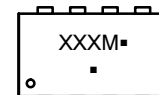
|                                                                                                              |                                                                                                                              |                                                                                                                  |                                                                                                                                       |                                                                                                                  |                                                                                                                        |
|--------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------|
| STYLE 1:<br>PIN 1. DRAIN<br>2. DRAIN<br>3. DRAIN<br>4. GATE<br>5. SOURCE<br>6. DRAIN<br>7. DRAIN<br>8. DRAIN | STYLE 2:<br>PIN 1. SOURCE 1<br>2. GATE 1<br>3. SOURCE 2<br>4. GATE 2<br>5. DRAIN 2<br>6. DRAIN 2<br>7. DRAIN 1<br>8. DRAIN 1 | STYLE 3:<br>PIN 1. ANODE<br>2. ANODE<br>3. SOURCE<br>4. GATE<br>5. DRAIN<br>6. DRAIN<br>7. CATHODE<br>8. CATHODE | STYLE 4:<br>PIN 1. COLLECTOR<br>2. COLLECTOR<br>3. COLLECTOR<br>4. BASE<br>5. EMITTER<br>6. COLLECTOR<br>7. COLLECTOR<br>8. COLLECTOR | STYLE 5:<br>PIN 1. ANODE<br>2. ANODE<br>3. DRAIN<br>4. DRAIN<br>5. SOURCE<br>6. GATE<br>7. CATHODE<br>8. CATHODE | STYLE 6:<br>PIN 1. ANODE<br>2. DRAIN<br>3. DRAIN<br>4. GATE<br>5. SOURCE<br>6. DRAIN<br>7. DRAIN<br>8. CATHODE / DRAIN |
|--------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------|

SOLDERING FOOTPRINT



Basic Style

GENERIC  
MARKING DIAGRAM\*



XXX = Specific Device Code  
M = Month Code  
▪ = Pb-Free Package  
(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

OPTIONAL SOLDERING FOOTPRINTS ON PAGE 2

|                  |             |                                                                                                                                                                                     |
|------------------|-------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| DOCUMENT NUMBER: | 98AON03078D | Electronic versions are uncontrolled except when accessed directly from the Document Repository.<br>Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| DESCRIPTION:     | ChipFET     | PAGE 1 OF 2                                                                                                                                                                         |

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

ADDITIONAL SOLDERING FOOTPRINTS\*



Styles 1 and 4



Style 2



Style 3



Style 5

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

|                  |             |                                                                                                                                                                                     |
|------------------|-------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| DOCUMENT NUMBER: | 98AON03078D | Electronic versions are uncontrolled except when accessed directly from the Document Repository.<br>Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| DESCRIPTION:     | ChipFET     | PAGE 2 OF 2                                                                                                                                                                         |

**onsemi** and **onsemi** are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

**onsemi**, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

### TECHNICAL PUBLICATIONS:

Technical Library: [www.onsemi.com/design/resources/technical-documentation](http://www.onsemi.com/design/resources/technical-documentation)  
onsemi Website: [www.onsemi.com](http://www.onsemi.com)

### ONLINE SUPPORT: [www.onsemi.com/support](http://www.onsemi.com/support)

For additional information, please contact your local Sales Representative at  
[www.onsemi.com/support/sales](http://www.onsemi.com/support/sales)